

FIG. 1(a)

FIG. 1(b)

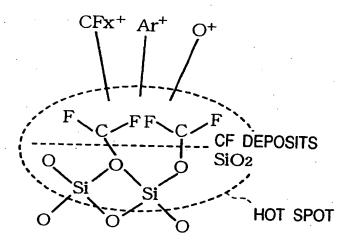


FIG. 1(c)

$$\begin{cases}
F & \text{Si-F } C = 0 \\
F & \text{SiO2}
\end{cases}$$

DECOMPO-SITION

## FIG. 3(a)

## FIG. 3(b)

(b) 
$$F = C = C = H$$
  $\Rightarrow$   $F = C = C = H$  No chemical reaction  $F = F$ 

## FIG. 3(c)

(c) 
$$H - C - C - H \Rightarrow H - C - C - O - H$$
  
 $H + H + STABLE$ 

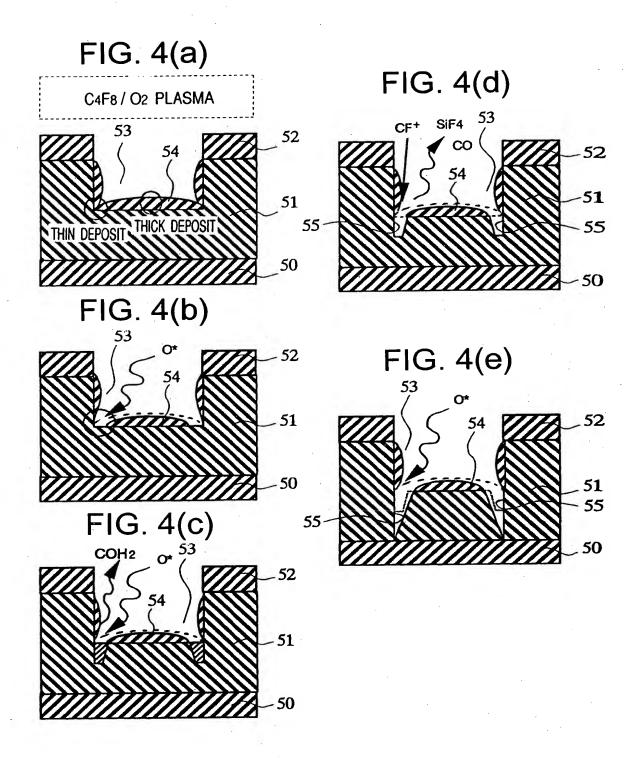


FIG. 5(a) REPULSION 
$$2eV$$

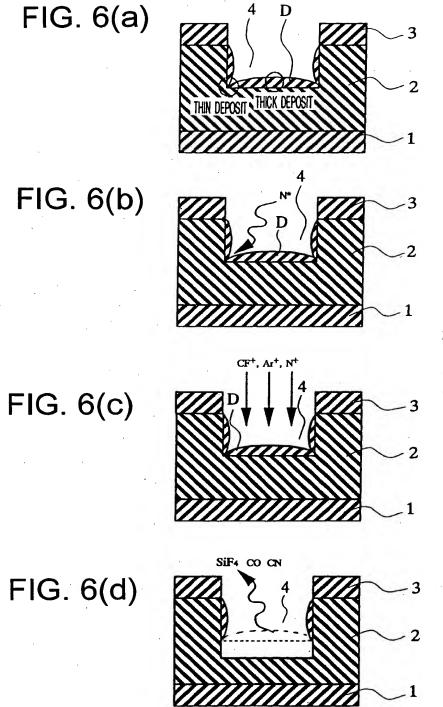
N\*

N\*

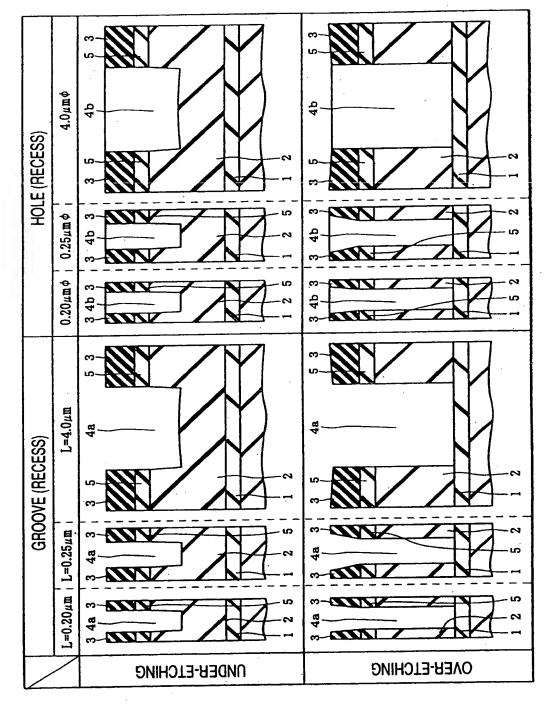
O

Si

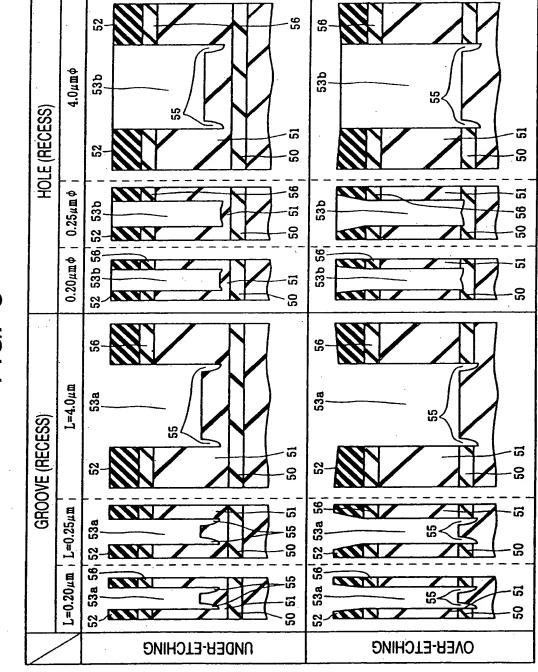
CH3



- 1: INSULATING FILM
- 2: ORGANIC INSULATING FILM
- 3: PHOTORESIST FILM
- 4: RECESS

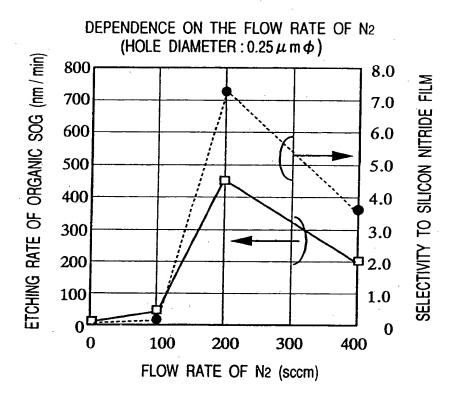


F1G. 7



F/G. 8

FIG. 9



- ☐ ETCHING RATE OF ORGANIC SOG (nm/min)
- SELECTIVITY TO SILICON NITRIDE FILM

FIG. 10

	CF GAS ALONE	CF GAS/O2	CF GAS/N2
ETCHING RATE	×	0	0
SELECTIVITY	×	×	0
FORM	$\nabla$	O ×	0
ELIMINATION PROPERTY	×	0	0
SYNTHETIC EVALUATION	×	$\nabla$	0

FIG. 11

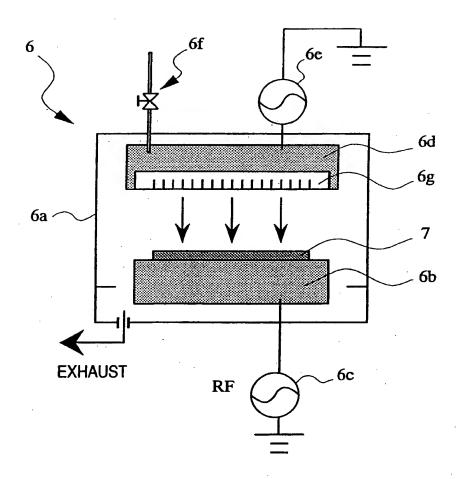
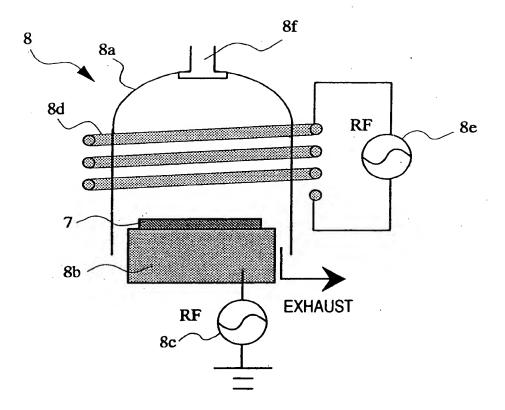
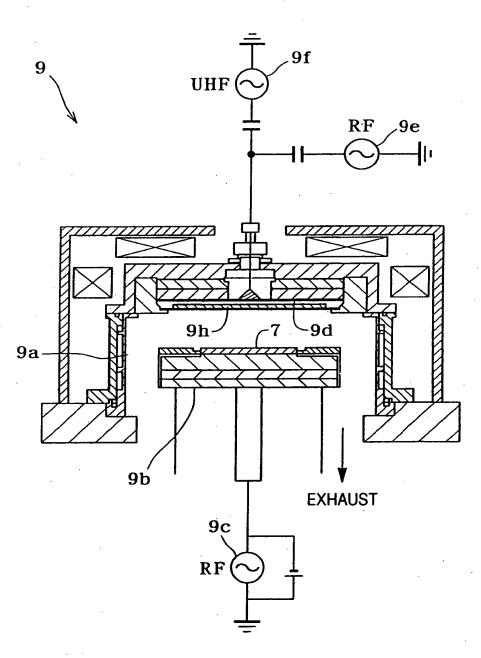


FIG. 12







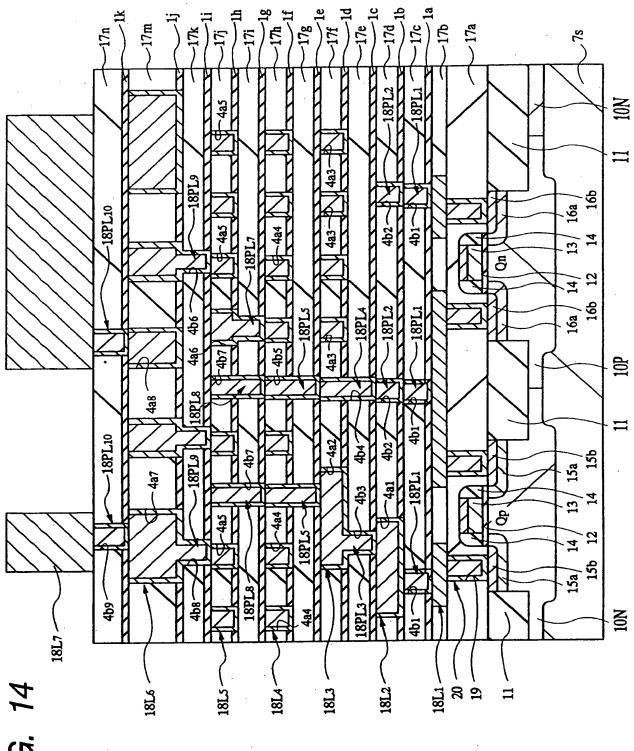
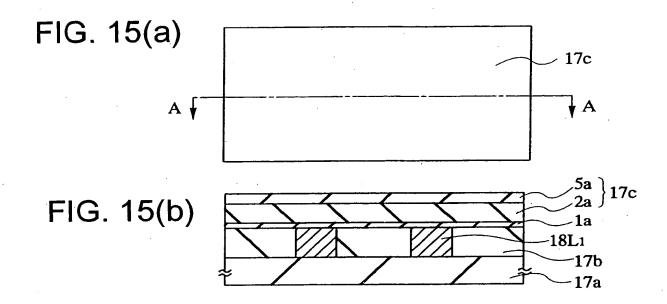
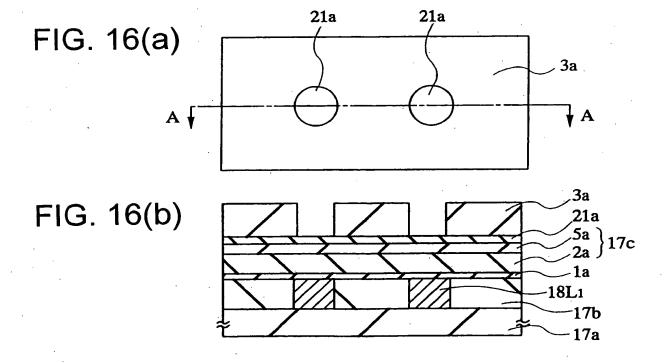
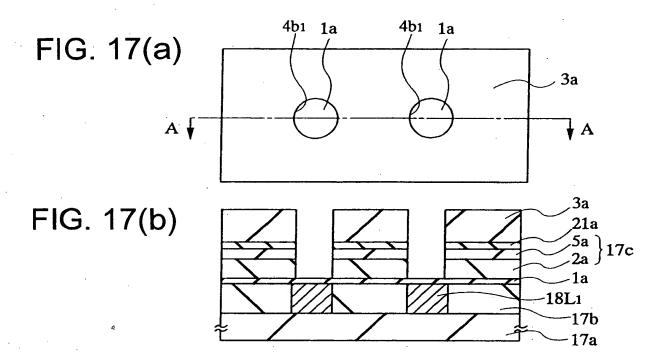
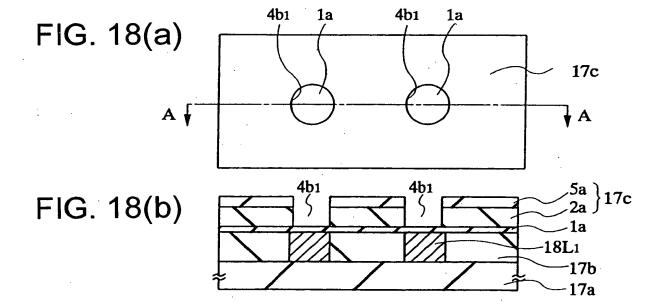


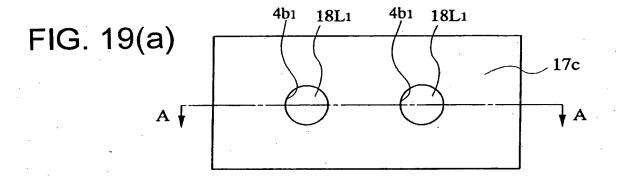
FIG.

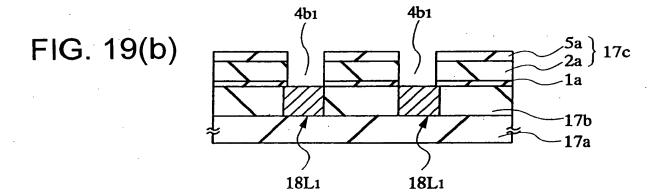


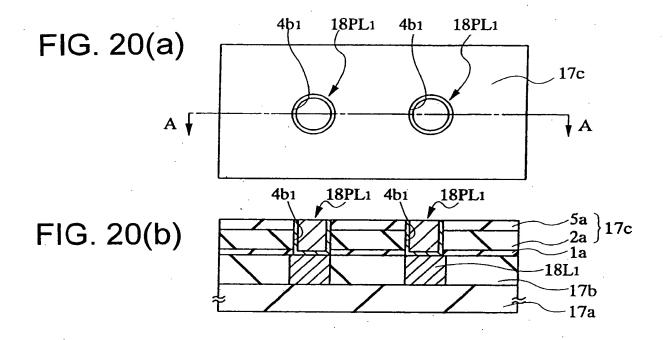


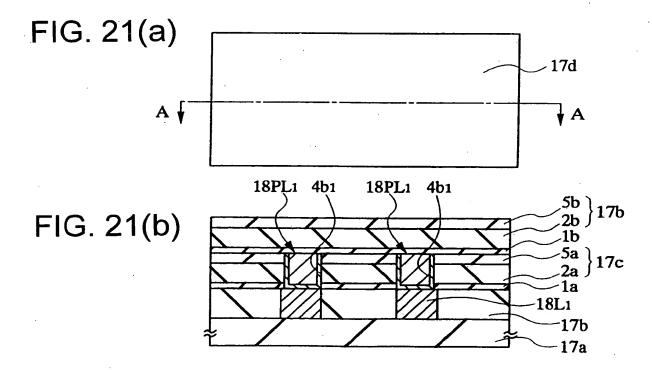


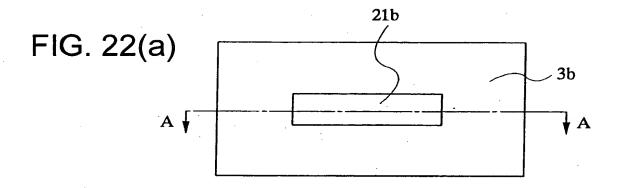


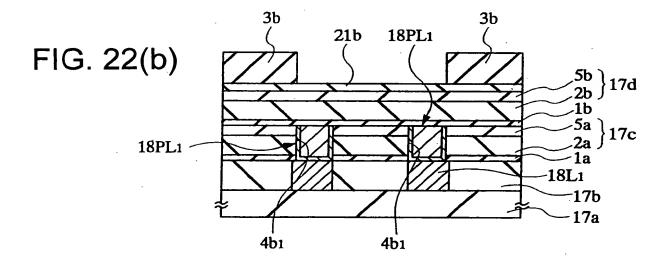


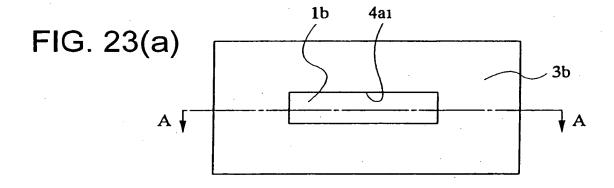


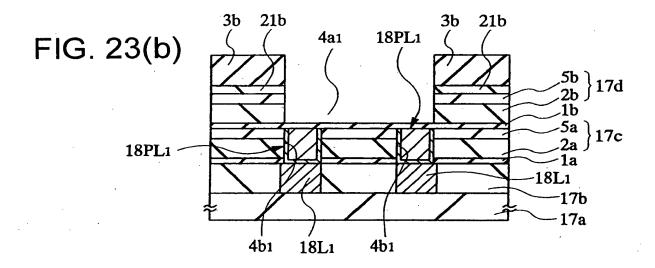


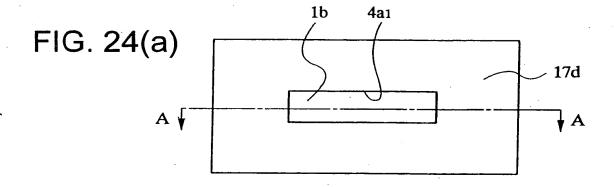


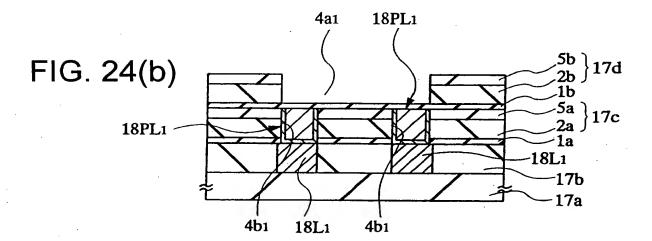


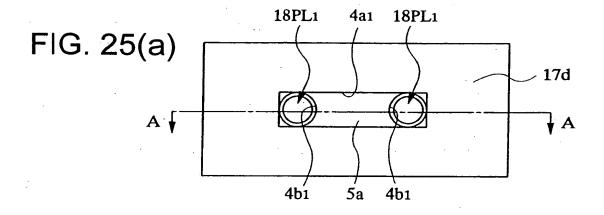


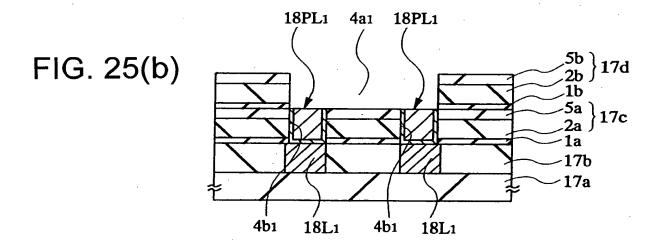


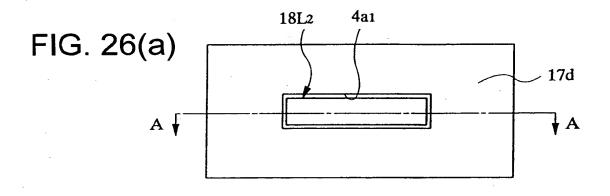


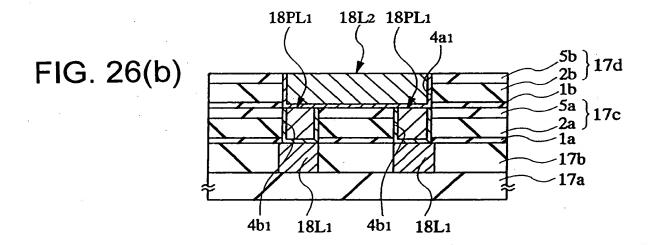


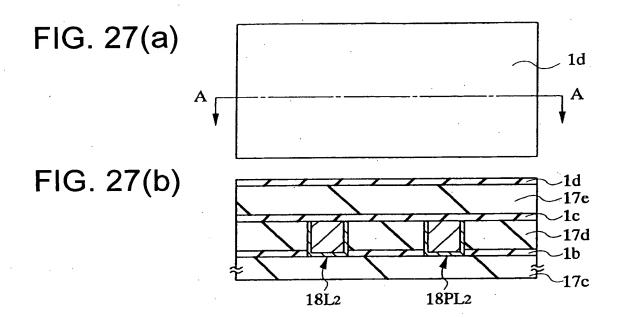


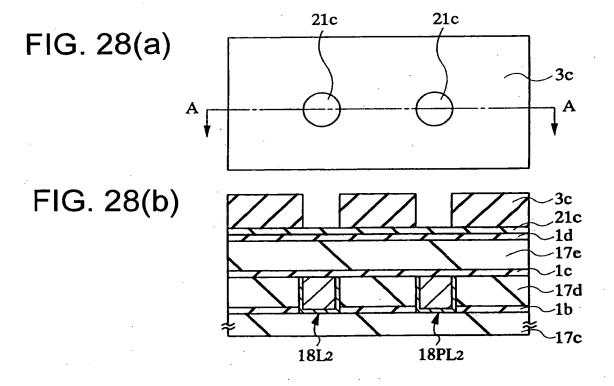


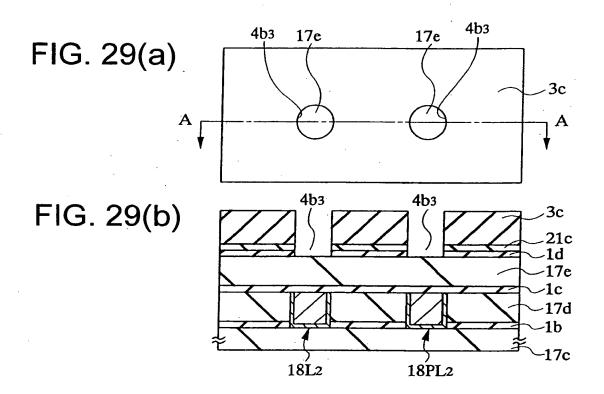


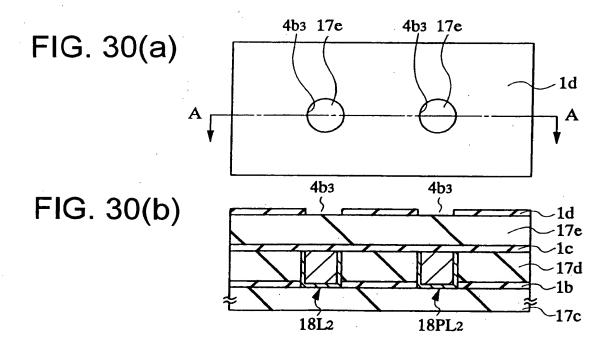


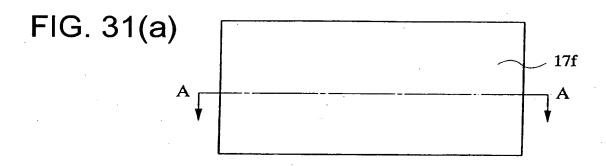


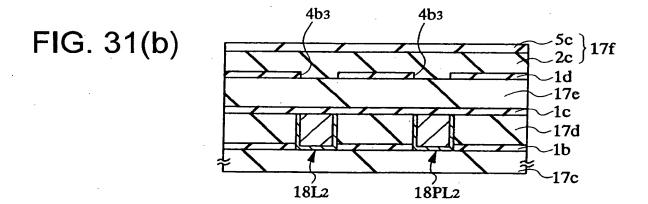


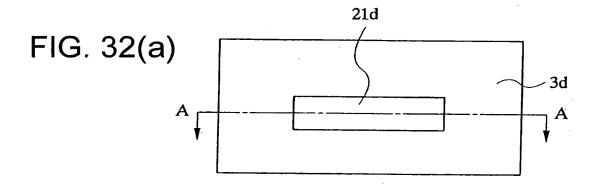


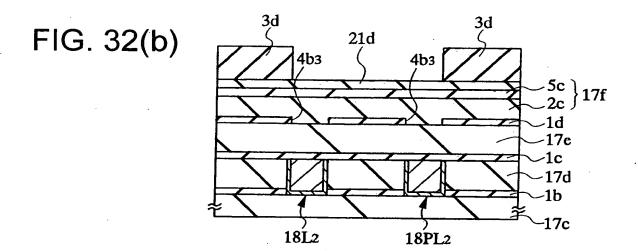


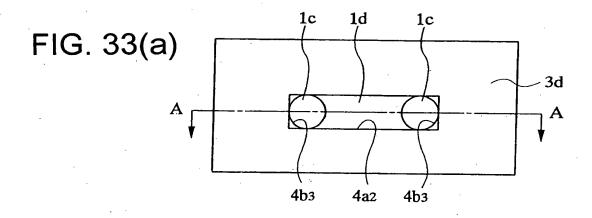


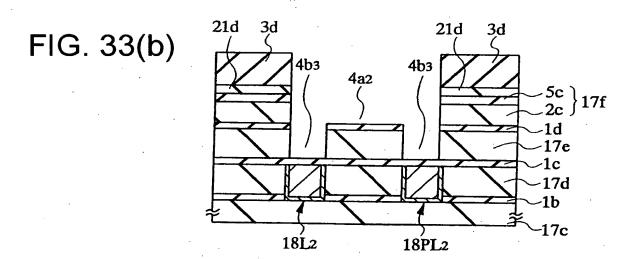


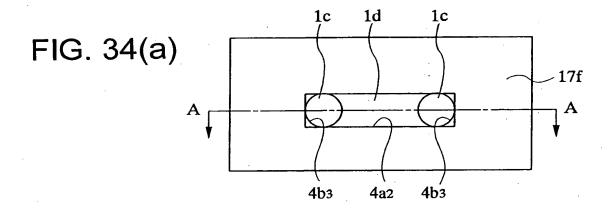


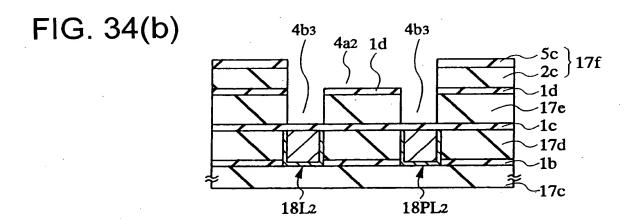


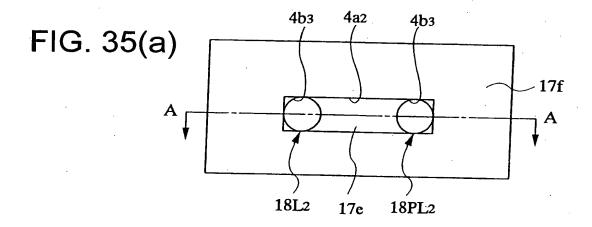


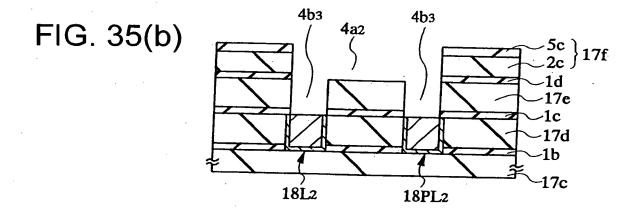


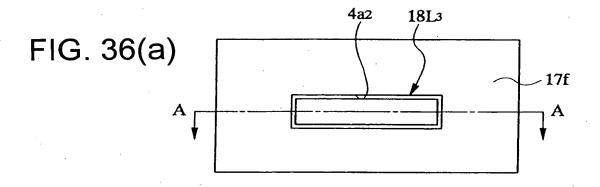


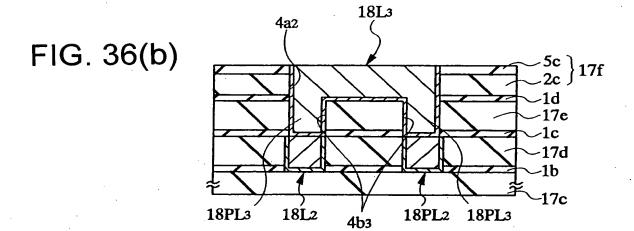


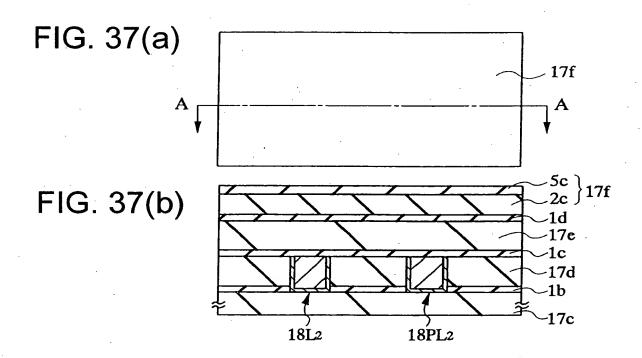


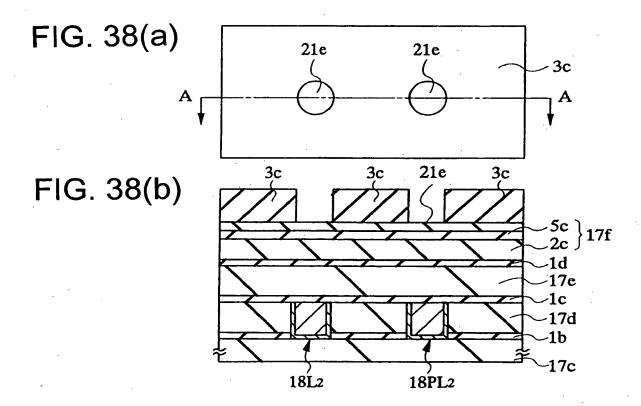


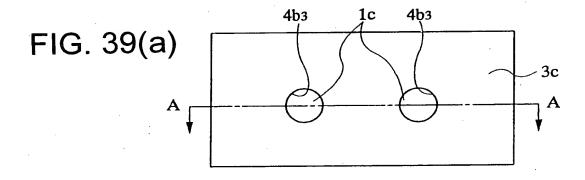


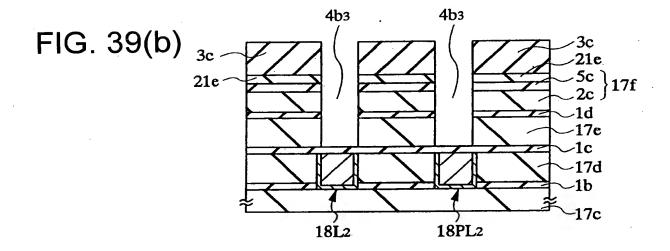


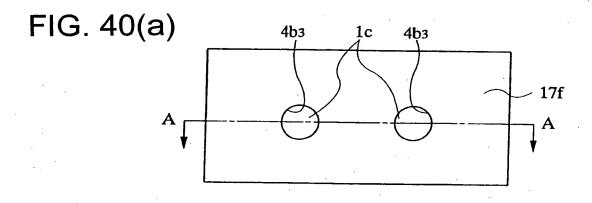


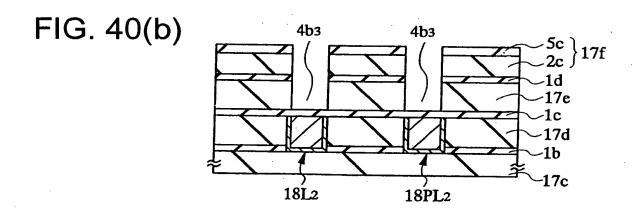


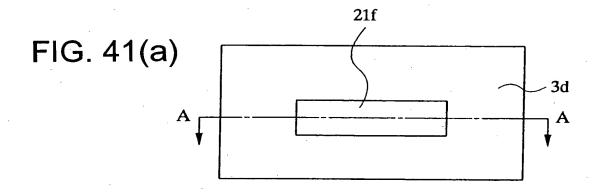


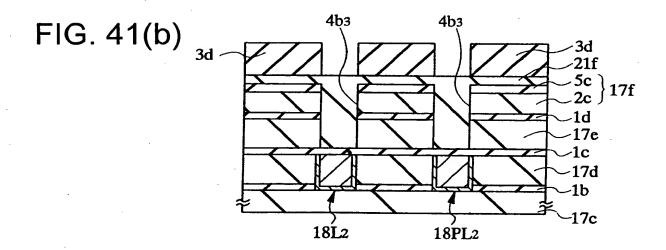


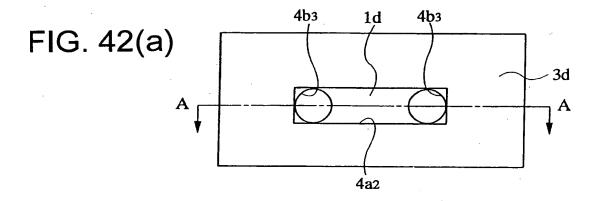


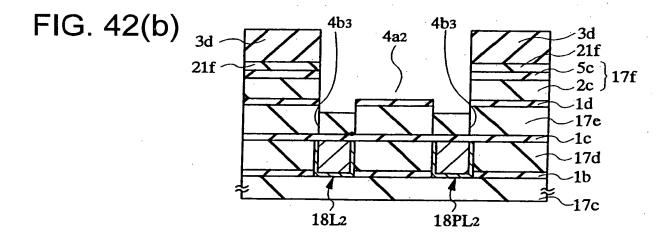


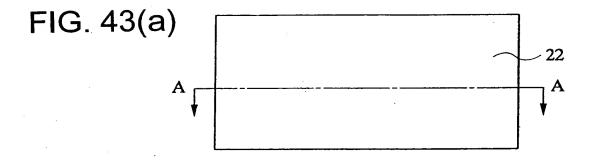


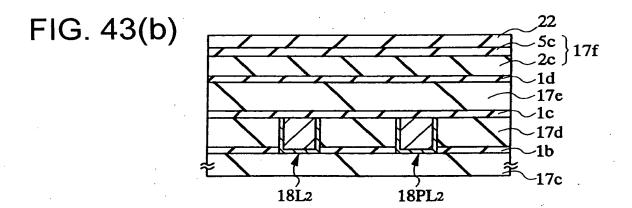


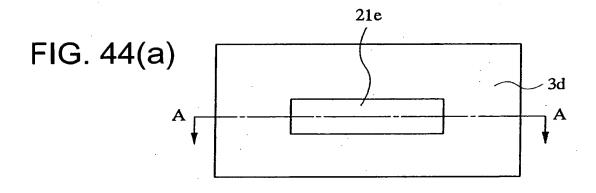


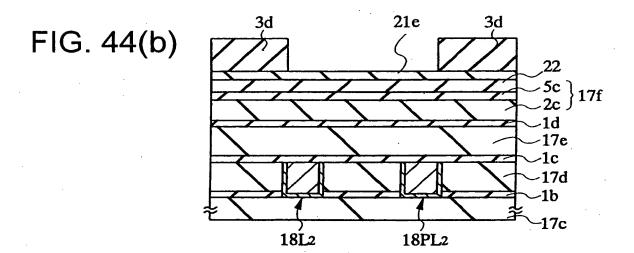


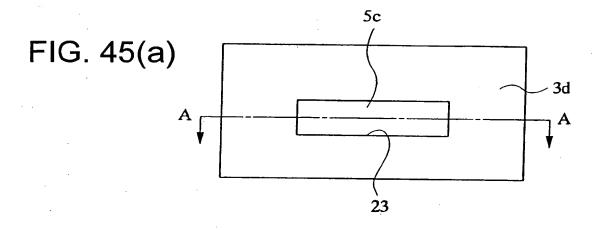


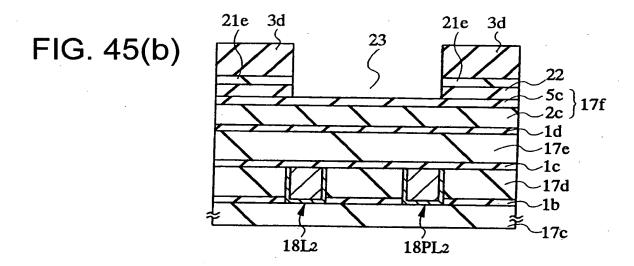


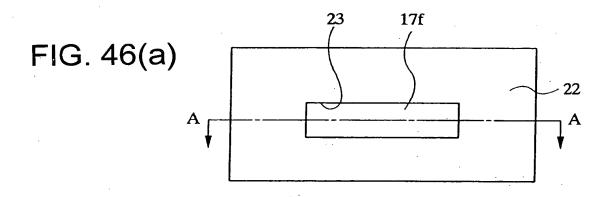


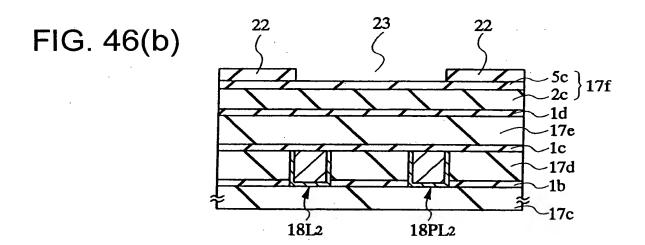


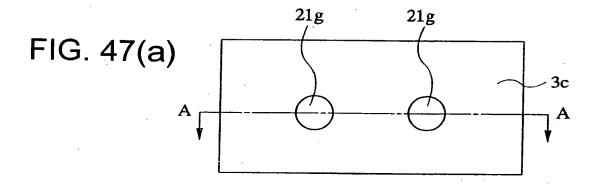


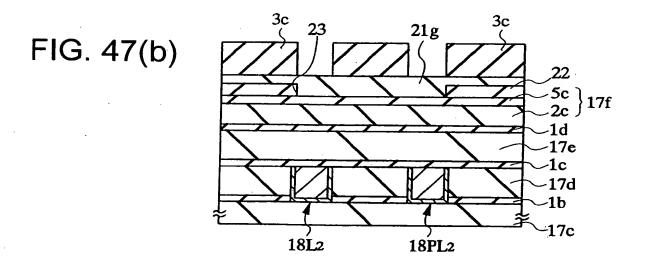


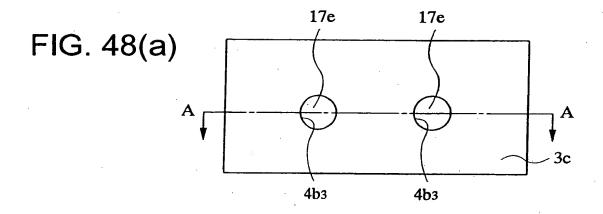


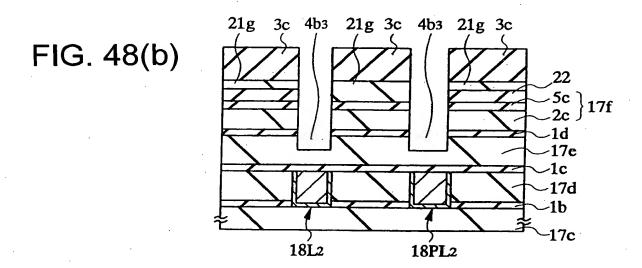


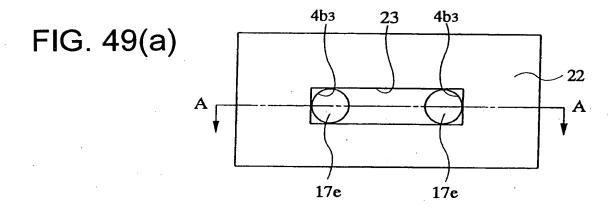


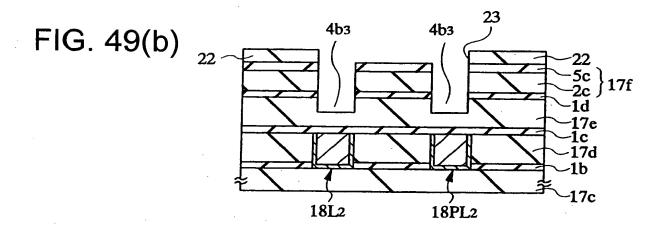


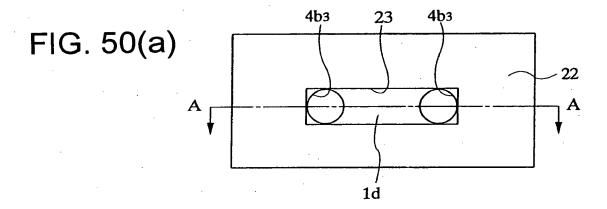


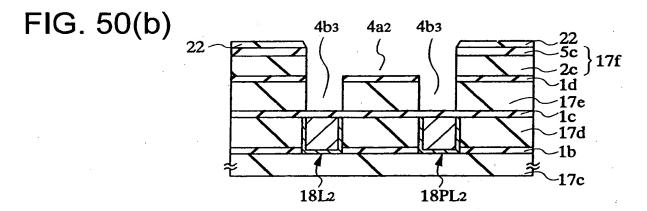


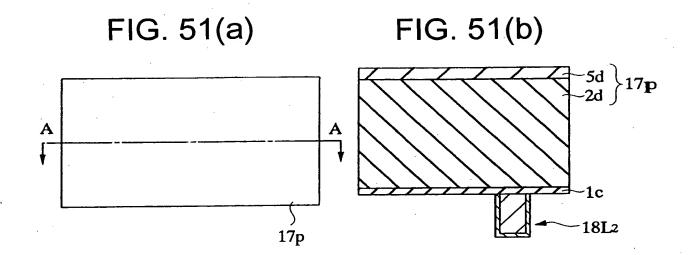


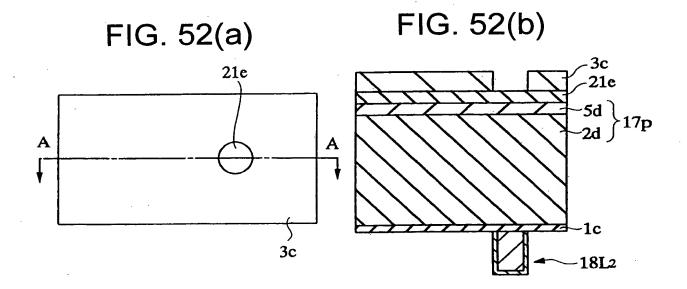


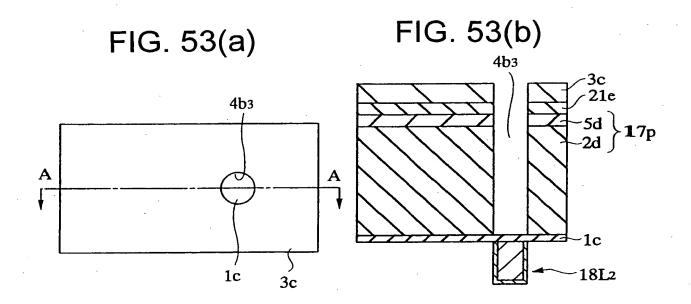


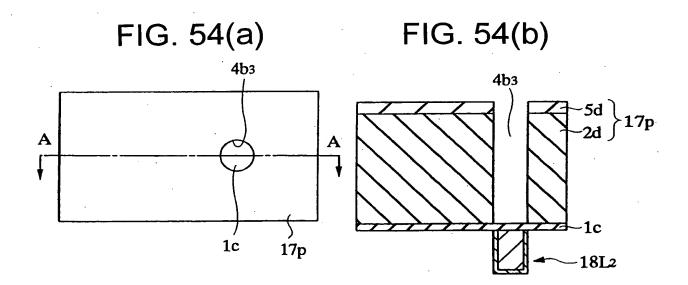


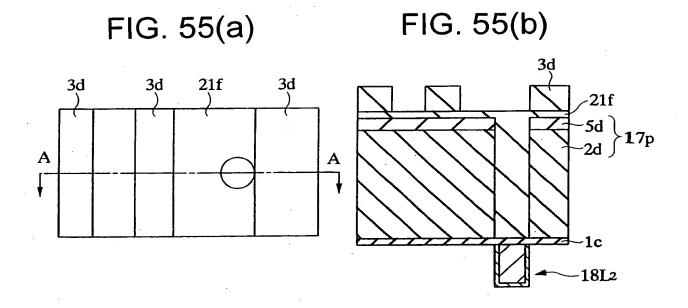


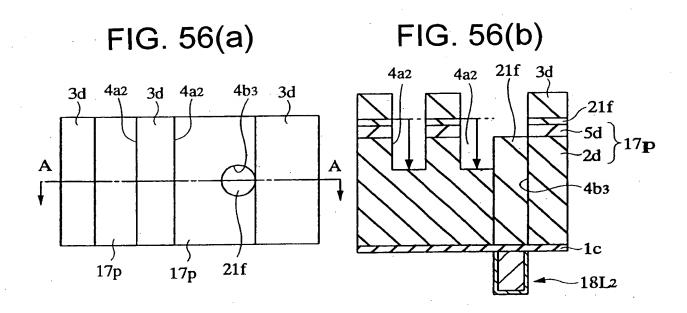


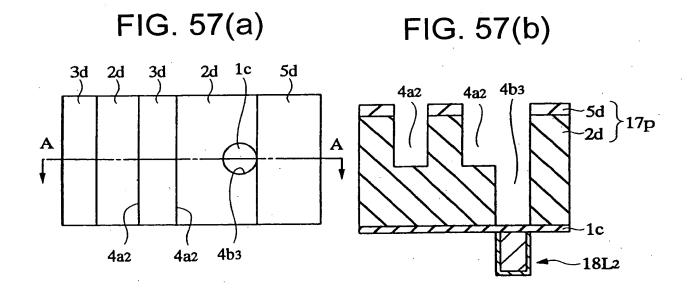


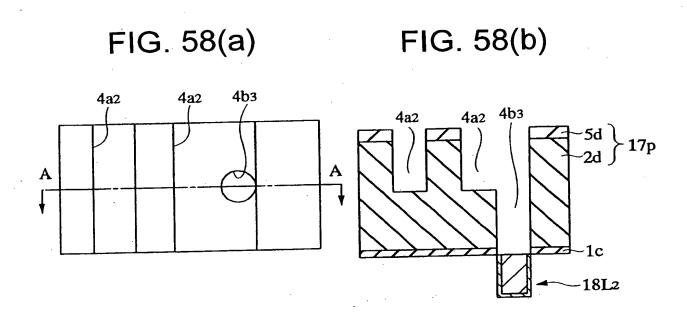


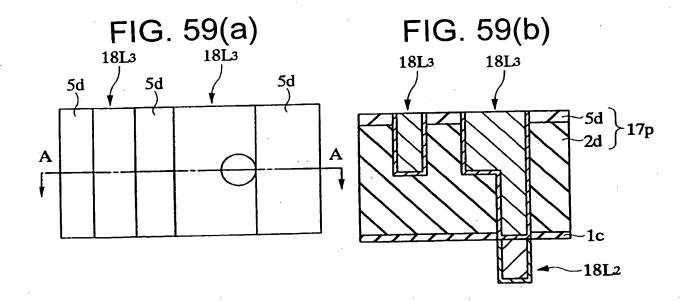












F/G. 60

	C4F8 FLOW RATE > O2 FLOW RATE	C4F8 FLOW RATE ≤ O2 FLOW RATE
SCHEMATIC CROSS- SECTIONAL VIEW	4	55 55
FORM		(HAVING A SIDE TRENCH)
SELECTIVITY TO SIN	X (NOT GREATER THAN 2)	(NOT GREATER THAN 5)
ETCHING APPARATUS	TOKYO ELECTRON IEM	CTRON IEM
ETCHING GAS	C4F8/02/Ar	)2/Ar
PRESSURE	2 5 mTorr	3 0 mTorr
HIGH-FREQUENCY POWER	500/200W	2200/1400W
STAGE TEMPERATURE	7	-20°C

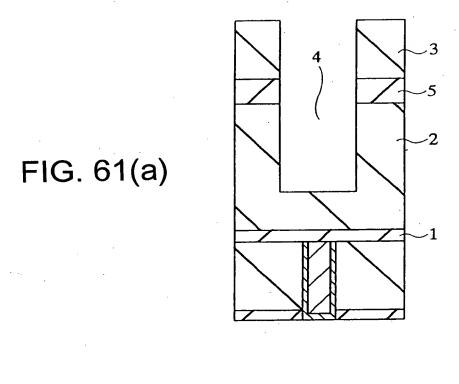


FIG. 61(b)

FIG. 62(a)

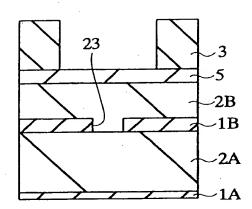


FIG. 62(b)

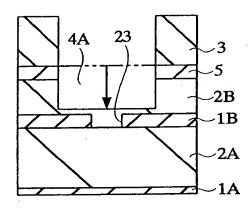
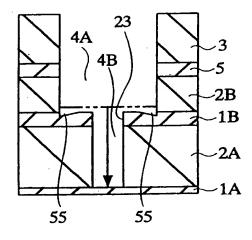
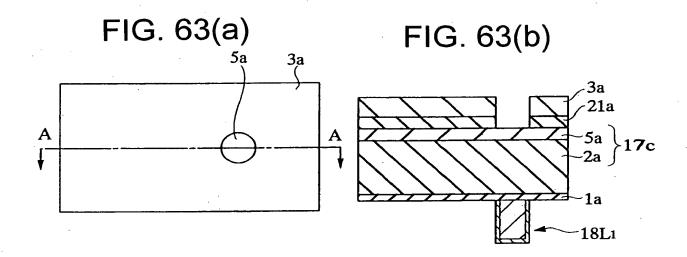
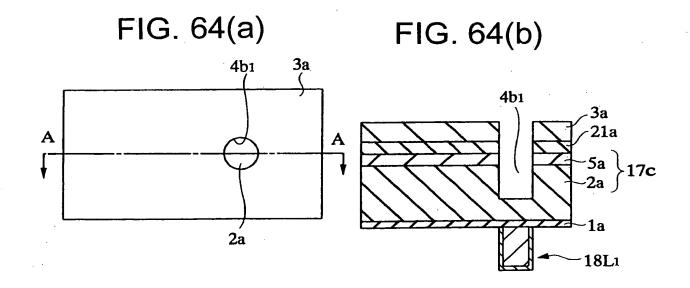
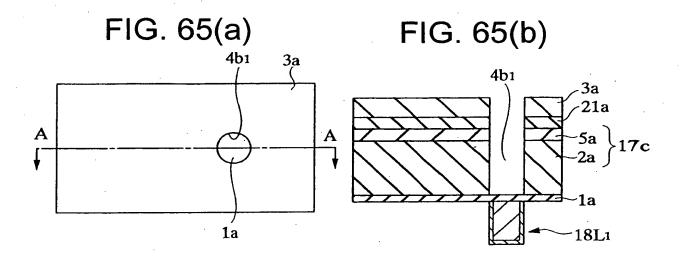


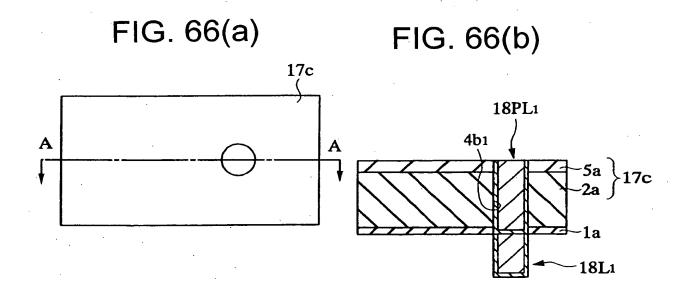
FIG. 62(c)

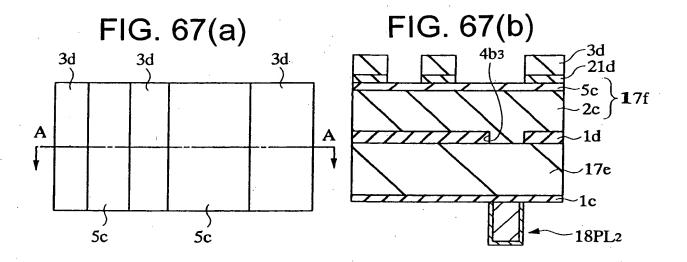


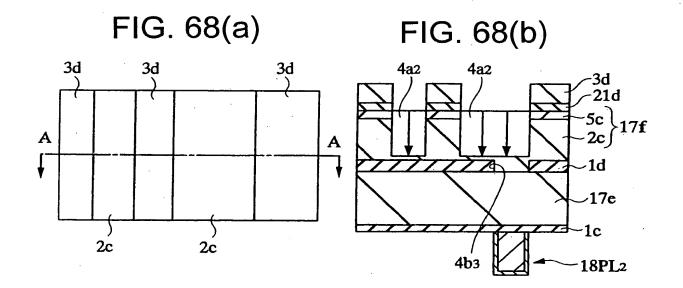


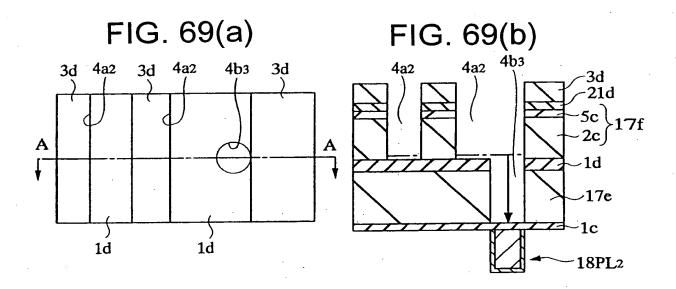


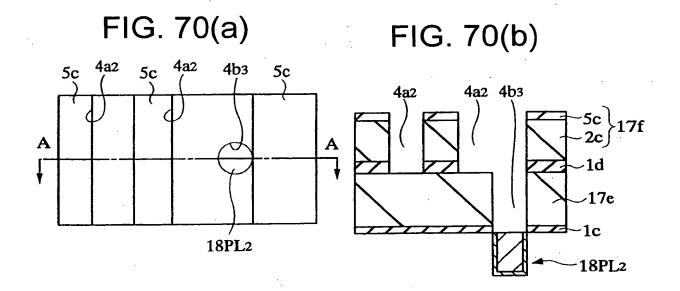


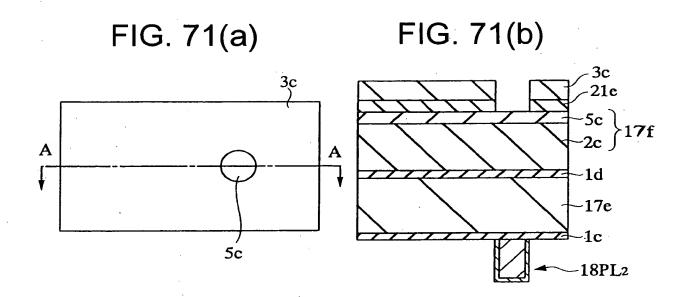


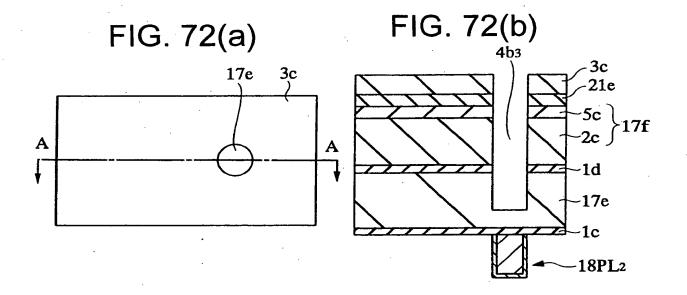


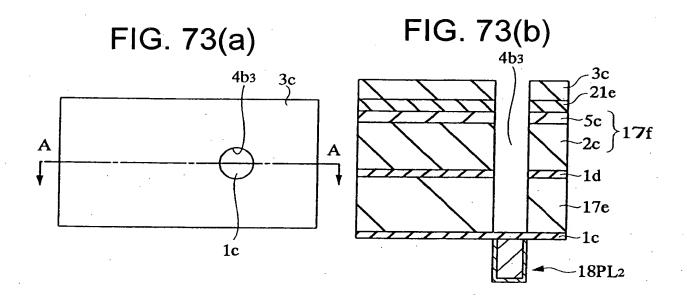


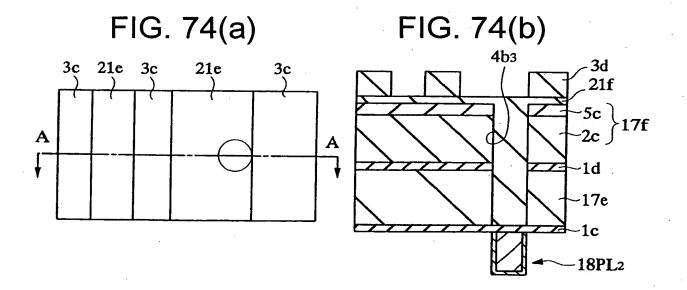


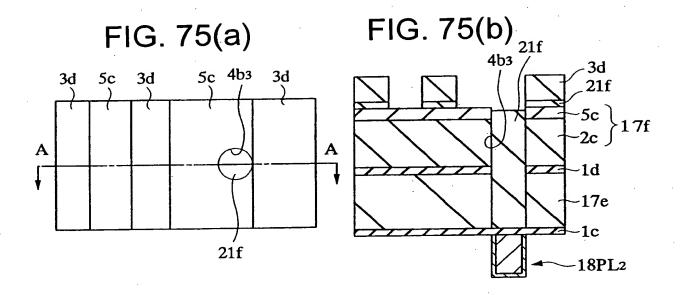


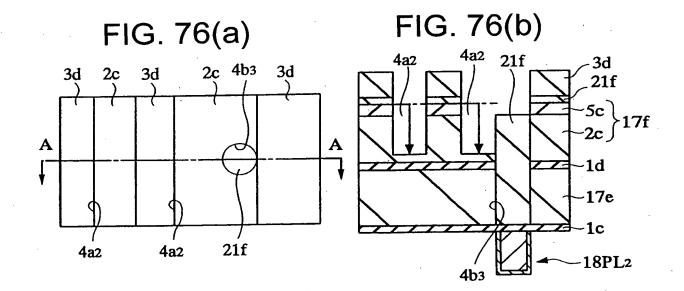


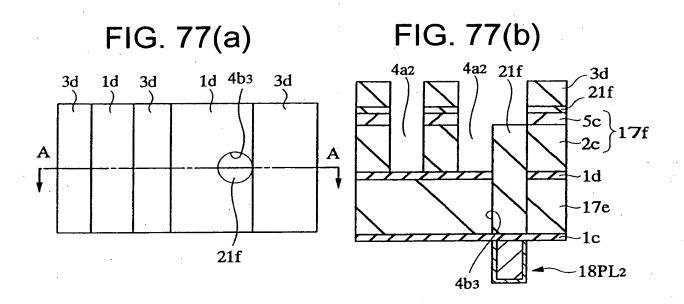


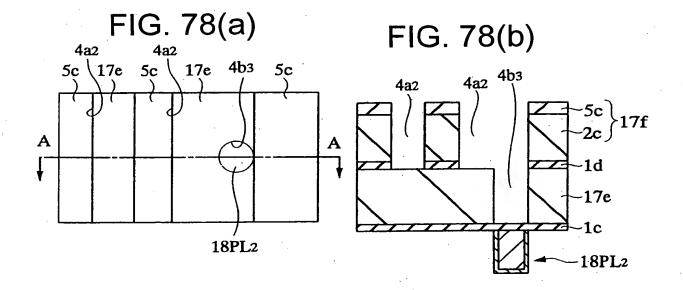


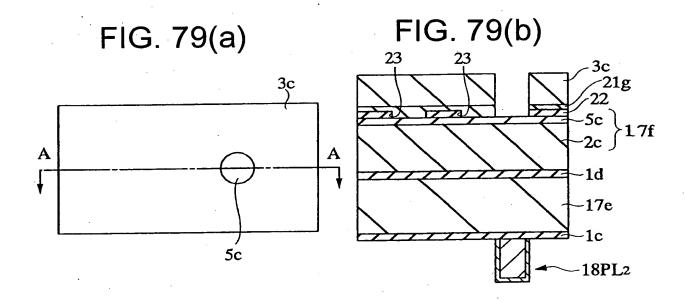


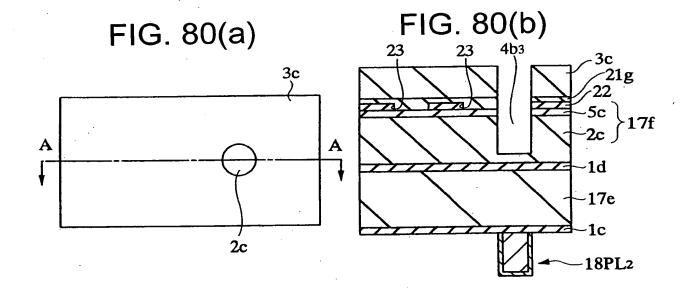


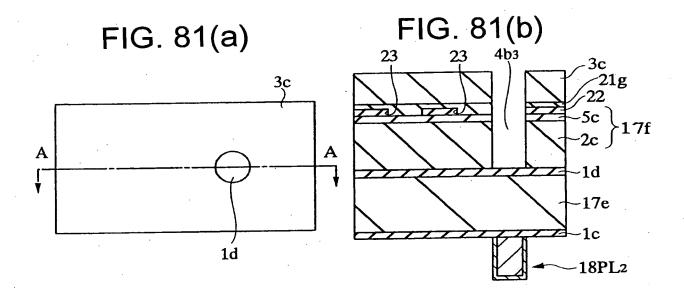


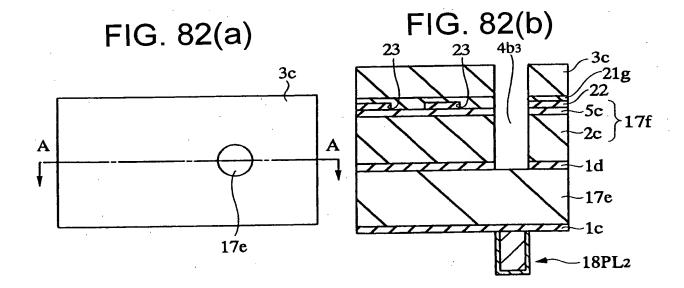


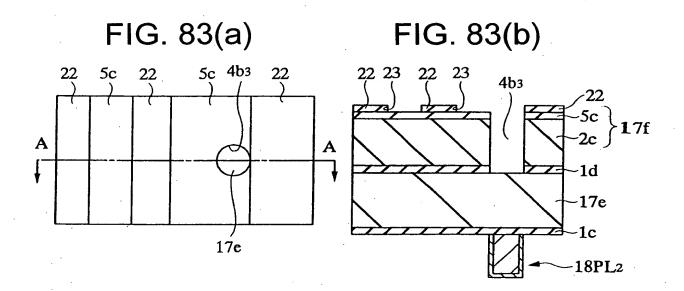


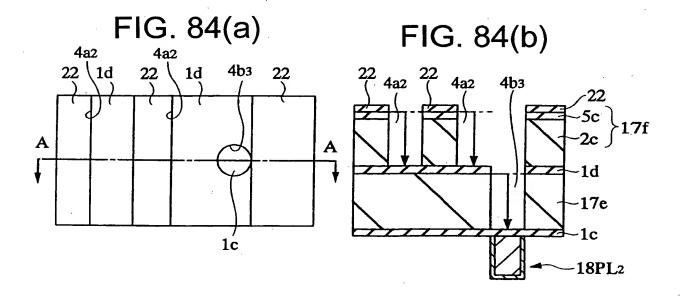


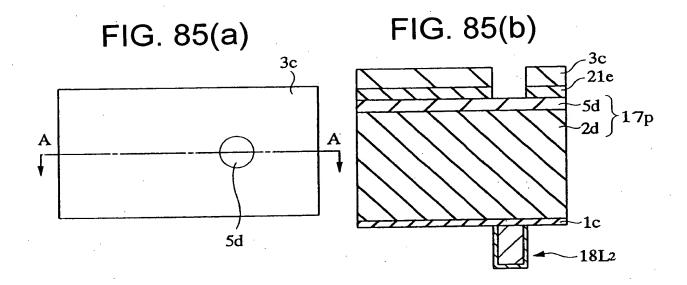


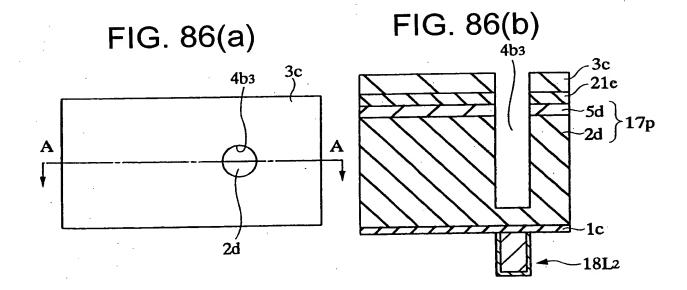


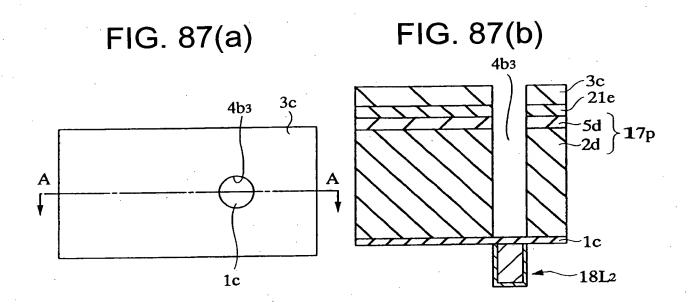


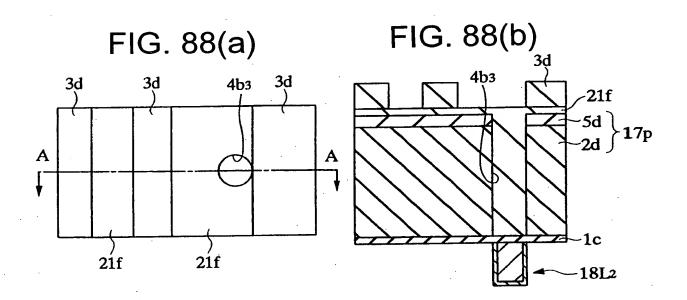


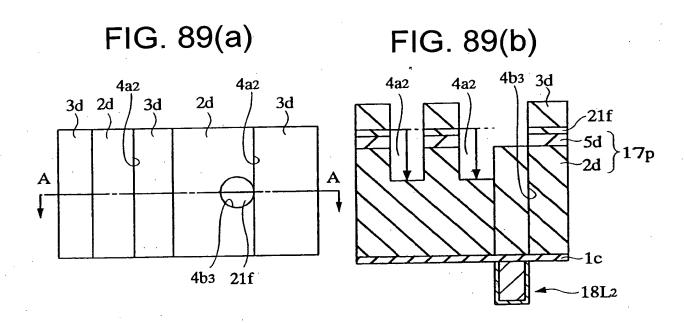


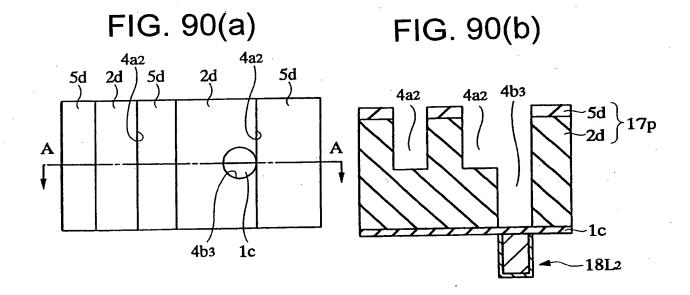












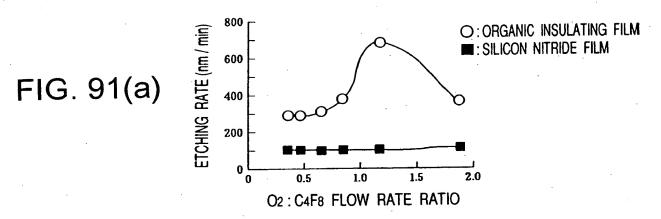
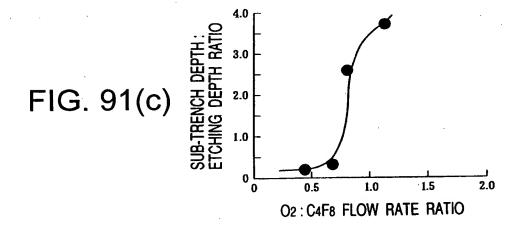


FIG. 91(b)

O2: C4F8 FLOW RATE RATIO	0.2	0.4	0.6	0.8	1.5
ETCHING FORM	4—————————————————————————————————————		4 C INSD- FILM	4	4



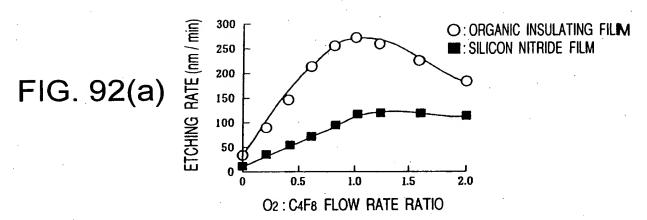
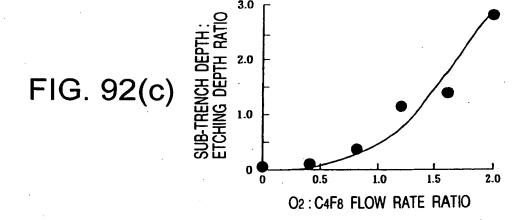
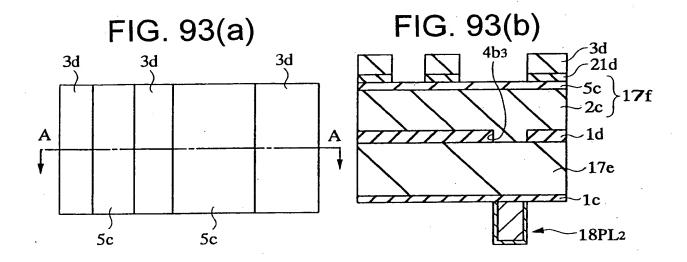
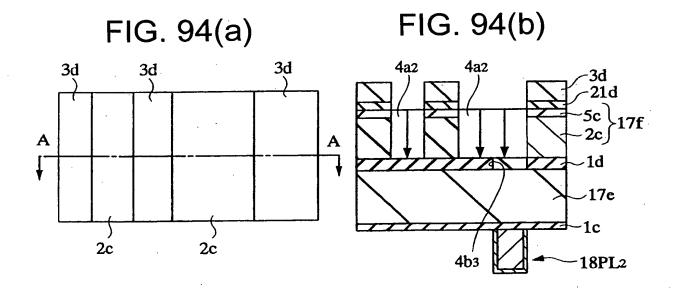


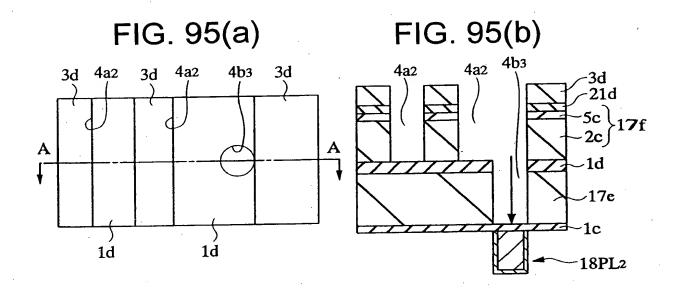
FIG. 92(b)

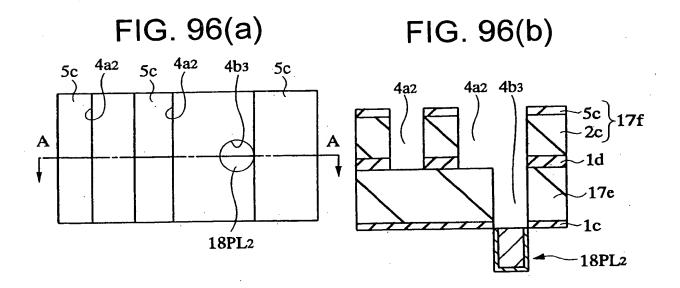
O2:C4F8 FLOW RATE RATIO	0	0.5	1.0	1.5	2.0
ETCHING FORM	TAPER ANGLE	ORGANIC LATING			

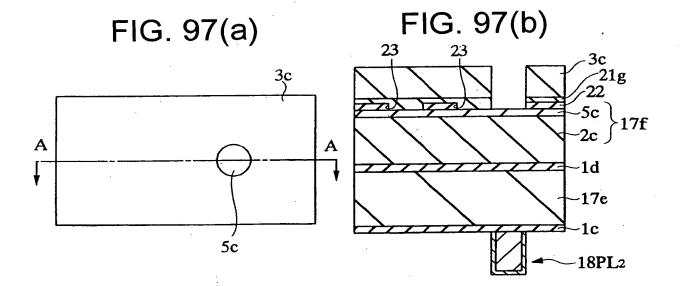


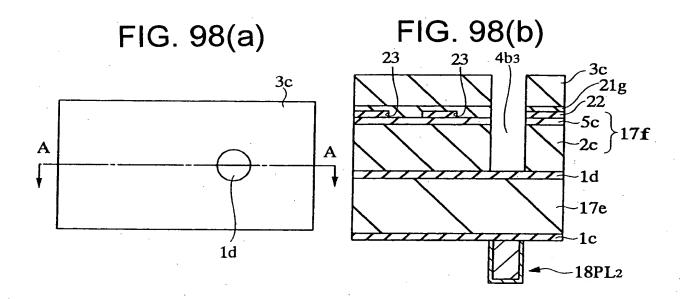


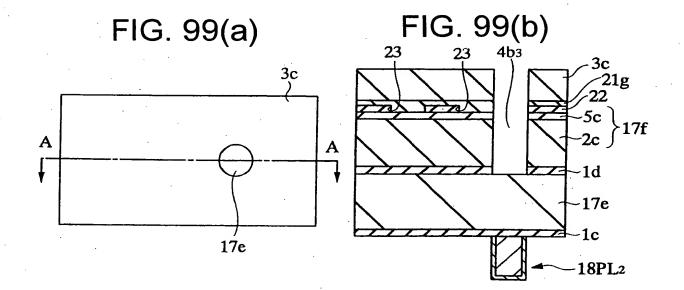


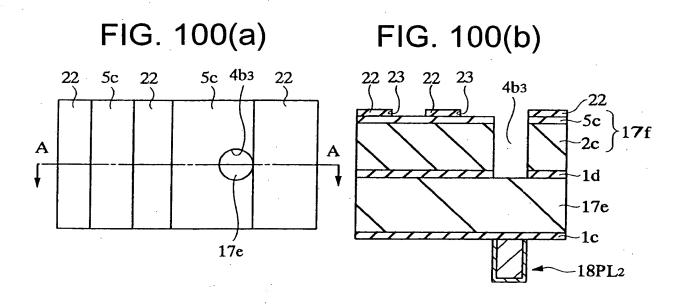












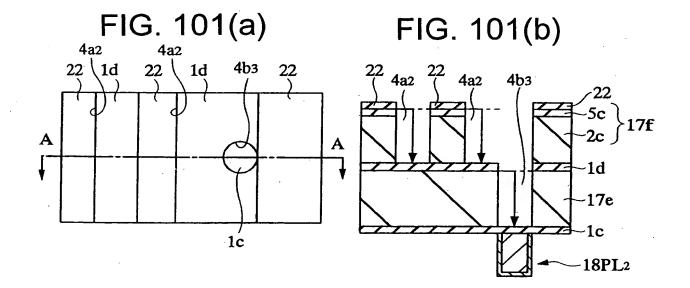
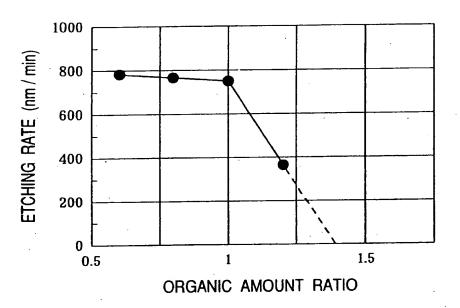
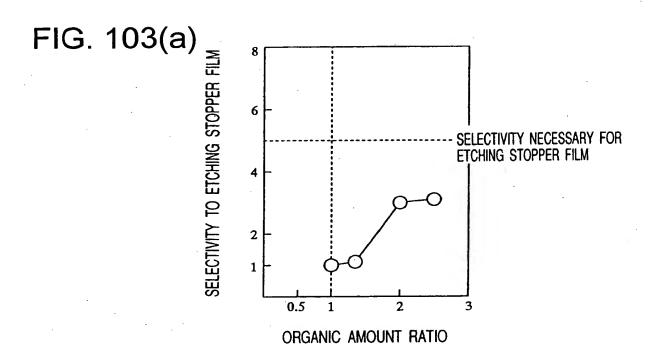
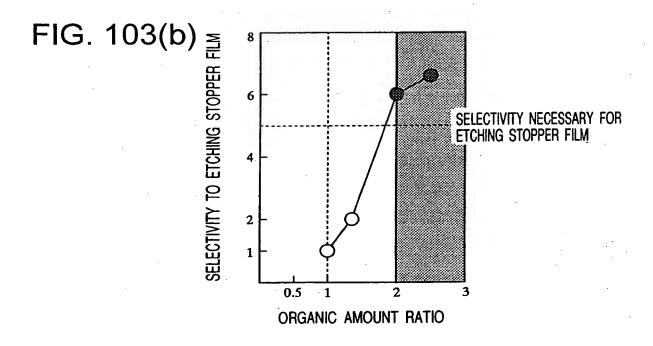


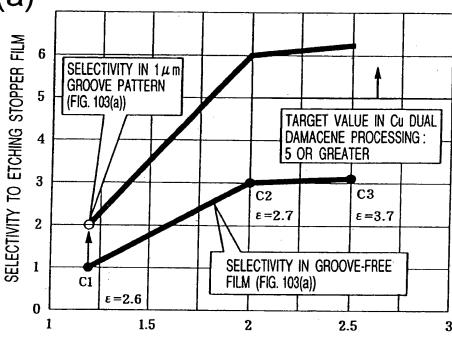
FIG. 102











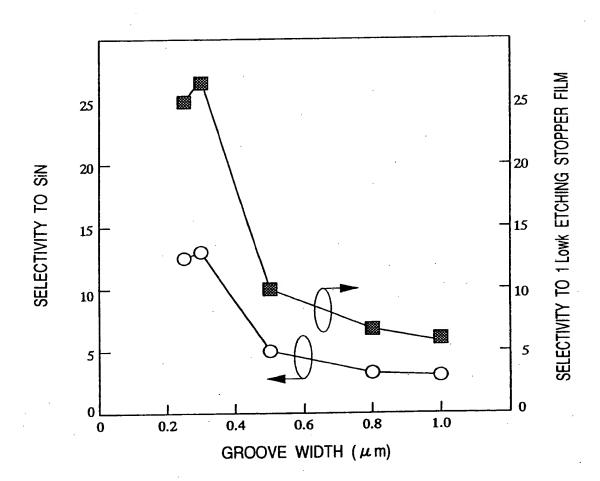
ORGANIC AMOUNT RATIO (SUPPOSING THAT THE ORGANIC INSULATIG FILM (USED AS AN INTERLEVEL INSULATING FILM) IS 1=20%

FIG. 104(b)

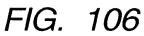
STRUCTURE OF C1 STRUCTURE OF C2, C3

$$CH_3$$
 $CH_3$ 
 $CH_3$ 

FIG. 105



SELECTIVITY TO ETCHING STOPPER FILM



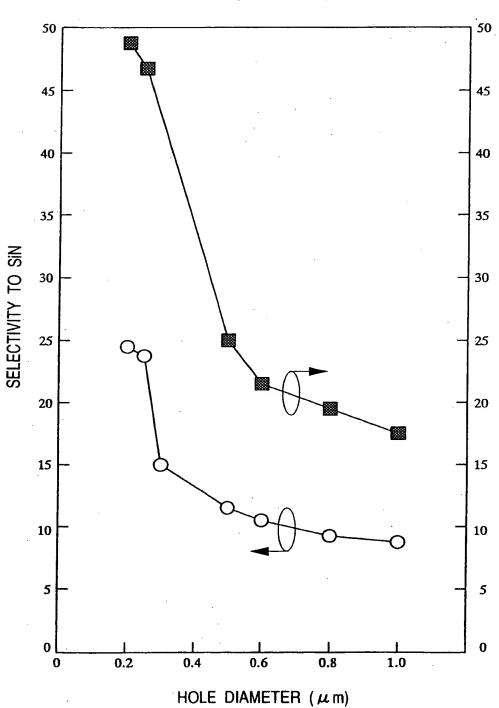


FIG. 107

	ADHESION	SELECTIVITY (TO ORGANIC SOG)	Cu DIFFUSION- PREVENTIVE LEAK PROPERTY	DIELECTRIC CONSTANT
NÏS	0	5~10	0	7.0
PTEOS	0	2~3	×	4.2
Blok	$\nabla$	5~10		5.0
Novel Etching Stopper Film	0	5~10		2.5~4.0

FIG. 108(a)

ORGANIC AMOUNT	CF CONSUM- PTION RATE*	AMOUNT OF CF DEPOSITS	ETCHING RATE
SMALL (LARGE SiO CONTENT)	HIGH	DEPOSITS: SMALL	HIGH
LARGE (SMALL SiO CONTENT)	LOW	DEPOSITS: LARGE	LOW

FIG. 108(b)

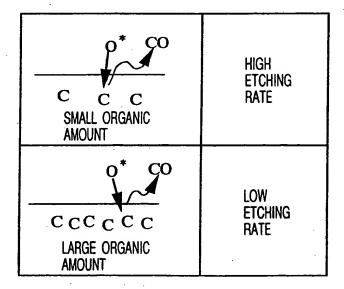


FIG. 109

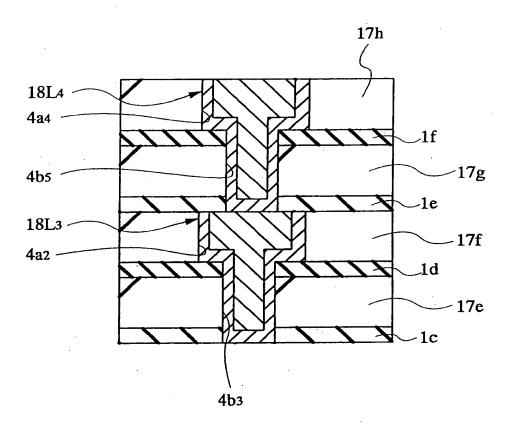


FIG. 110

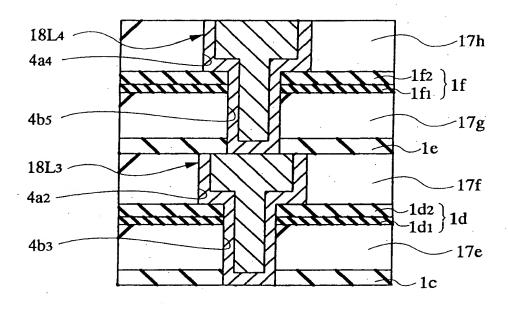


FIG. 111

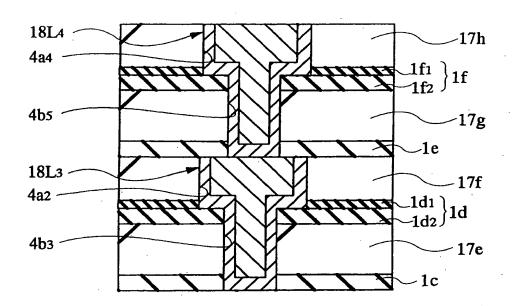


FIG. 112(a)

FIG. 112(b)

3c

21g

3c

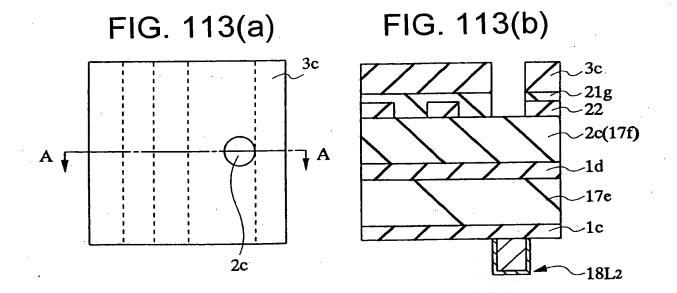
21g

22(17f)

1d

17e

18L2



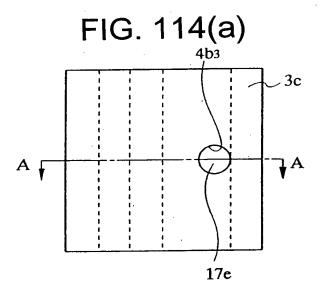


FIG. 114(b)

4b3

3c

21g

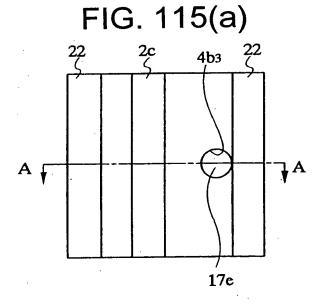
22c(17f)

1d

17e

1c

18L2



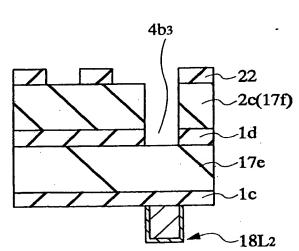


FIG. 115(b)

FIG. 116(a)

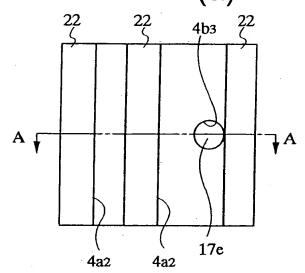


FIG. 116(b)

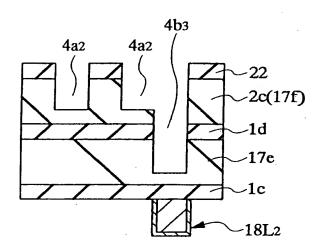


FIG. 117(a)

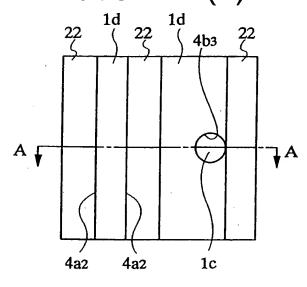


FIG. 117(b)

